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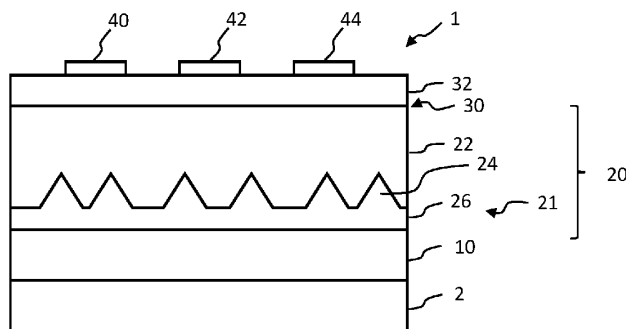


Fig. 5

(57) Abstract: A semiconductor structure (1), comprising: a substrate (2); a base layer (10), the base layer (10) comprising an AlGaIn layer, the base layer (10) being arranged above the substrate (2); at least one group of layers (20), the at least one group of layers (20) being arranged above the base layer (10), wherein each of the at least one group of layers (20) comprises: a first layer (21), the first layer (21) being a layer of InGaIn and comprising quantum dots (24); a second layer (22), the second layer (22) being a layer of InGaIn, the second layer (22) being arranged on and above the first layer (21), wherein the second layer (22) laterally encloses the quantum dots (24) of the first layer (21), wherein a material composition of the InGaIn of the second layer (22) is different from a material composition of the InGaIn of the first layer (21).



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